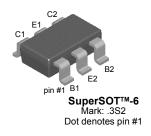


# FMBM5551 NPN General Purpose Amplifier

- · This device has matched dies
- · Sourced from process 16.
- · See MMBT5551 for characteristics

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## **Absolute Maximum Ratings \***

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	160	V
V <sub>CBO</sub>	Collector-Base Voltage 180		V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current (DC)	600	mA
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> = 25°C)	0.7	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature Range	-55 ~ 150	°C
$T_{\thetaJA}$	Thermal Resistance, Junction to Ambient	180	°C/W

<sup>\*</sup> Pd total, for both transistors. For each transistor, Pd = 350mW

### Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Max	Units		
Off Charact	Off Characteristics						
BV <sub>CEO</sub>	Collector-Emitter Voltage	I <sub>C</sub> = 1mA, I <sub>B</sub> = 0	160		V		
BV <sub>CBO</sub>	Collector-Base Voltage	I <sub>C</sub> = 100μA, I <sub>E</sub> = 0	180		V		
BV <sub>EBO</sub>	Emitter-Base Voltage	$I_C = 10\mu A, I_C = 0$	6		V		
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = 120V V <sub>CB</sub> = 120V, T <sub>a</sub> = 100°C		50 50	nA μA		
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = 4V		50	nA		
On Characteristics							
h <sub>FE1</sub>	DC Current Gain	V <sub>CE</sub> = 5V, I <sub>C</sub> = 1mA	80				
DIVID1	Variation Ratio of h <sub>FE1</sub> Between Die 1 and Die 2	h <sub>FE1</sub> (Die1)/h <sub>FE1</sub> (Die2)	0.9	1.1			
h <sub>FE2</sub>	DC Current Gain	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA	80	250			
DIVID2	Variation Ratio of h <sub>FE2</sub> Between Die 1 and Die 2	h <sub>FE2</sub> (Die1)/h <sub>FE2</sub> (Die2)	0.95	1.05			

## Electrical Characteristics (Continued) T<sub>C</sub> = 25°C unless otherwise noted

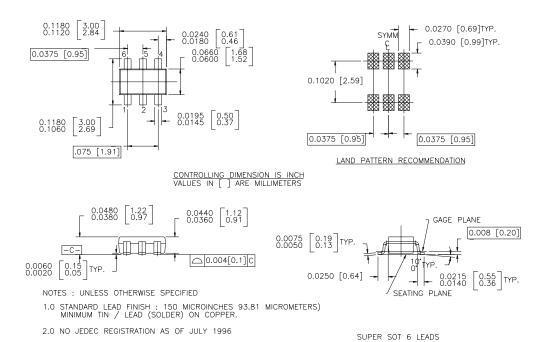
Symbol	Parameter	Conditions	Min.	Max	Units
h <sub>FE3</sub>	DC Current Gain	V <sub>CE</sub> = 5V, I <sub>C</sub> = 50mA	30		
DIVID3	Variation Ratio of h <sub>FE3</sub> Between Die 1 and Die 2	h <sub>FE3</sub> (Die1)/h <sub>FE3</sub> (Die2)	0.9	1.1	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA I <sub>C</sub> = 50mA, I <sub>B</sub> = 5mA		0.15 0.2	V V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA I <sub>C</sub> = 50mA, I <sub>B</sub> = 5mA		1 1	V V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA		1	V
DEL	Difference of V <sub>BE(on)</sub> Between Die1 and Die 2	V <sub>BE(on)</sub> (Die1)-V <sub>BE(on)</sub> (Die2)	-8	8	mV
Small Signa	al Characteristics			•	
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10V, f = 1MHz		6	pF
C <sub>ib</sub>	Input Capacitance	V <sub>CB</sub> = 0.5V, f = 1MHz		20	pF
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = 10V, I <sub>C</sub> = 10mA, f = 100MHz	100	300	MHz
NF	Noise Figure	$V_{CE} = 5V$ , $I_{C} = 200\mu A$ , $f = 1MHz$ , $R_{S} = 20K\Omega$ , $B = 200Hz$		8	dB
h <sub>fe</sub>	Small Signal Current Gain	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA, f = 1.0KHz	50	250	

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### **Mechanical Dimensions**

# SuperSOT™-6

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Dimensions in Millimeters

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FACT Quiet Series™		OCXPro™	RapidConnect™	UHC™
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